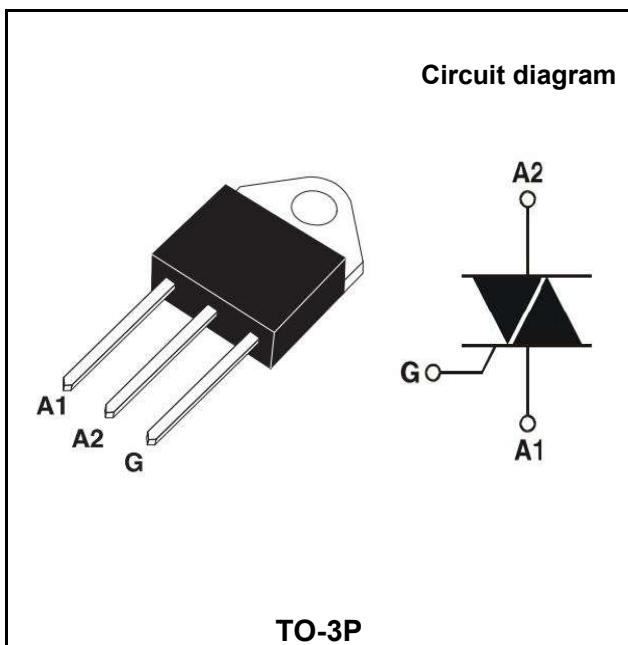


**40A 3Quadrants TRIACs**
**Product Summary**

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
$V_{DRM} V_{RRM}$	800/1200/1600	V
$V_{TM}$	1.55	V

**Features**

With high ability to withstand the shock loading of large current, With high commutation performances, 3 quadrants products especially recommended for use on inductive load


**Application**

Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

**Order Information**

Part Number	Package	Marking	Packing	Packing Quantity
BTA41-800BW	TO-3P	BTA41-800BW XXXX	box	600PCS/box
BTA41-1200BW	TO-3P	BTA41-1200BW XXXX	box	600PCS/box
BTA41-1600BW	TO-3P	BTA41-1600BW XXXX	box	600PCS/box

**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	$V_{DRM}$	800/1200/1600	V
Repetitive peak reverse voltage	$V_{RRM}$	800/1200/1600	V
RMS on-state current	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	$I_{TSM}$	400	A
$I^2t$ value for fusing (tp=10ms)	$I^2t$	880	$A^2s$
Critical rate of rise of on-state current ( $ IG  = 2 \times  GT $ )	$dI/dt$	50	$A/\mu s$
Peak gate current	$I_{GM}$	4	A
Average gate power dissipation	$P_G (AV)$	1	W
Junction Temperature	$T_J$	-40~+125	°C
Storage Temperature	$T_{STG}$	-40 ~+150	°C

## Electrical characteristics (TA=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition		Value		Unit
Gate trigger current	I <sub>GT</sub>	V <sub>D</sub> =12VR=33Ω	I - II - III	MAX.	50	mA
Gate trigger voltage	V <sub>GT</sub>			MAX.	1.3	V
Gate non-trigger voltage	V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C	I - II - III	MIN.	0.2	V
latching current	I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	MAX.	80	mA
Holding current	I <sub>H</sub>	I <sub>T</sub> =100mA	II	MAX.	100	mA
Critical-rate of rise of commutation voltage	dV <sub>D</sub> /dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125°C		MIN.	1000	V/μs

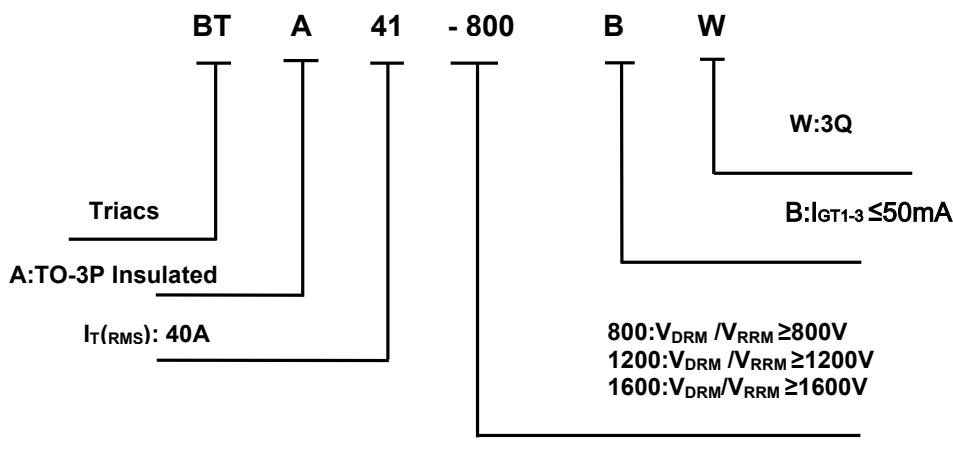
## STATIC CHARACTERISTICS

Forward "on" voltage	V <sub>TM</sub>	I <sub>TM</sub> =60A tp=380μs		MAX.	1.55	V
Repetitive Peak Off-State Current	I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C	MAX.	10	μA
Repetitive Peak Reverse Current	I <sub>RRM</sub>		T <sub>j</sub> =125°C	MAX.	5	mA

## THERMAL RESISTANCES

Thermal resistance	R <sub>th(j-c)</sub>	Junction to case	TYP.	0.9	°C/W
	R <sub>th(j-a)</sub>	Junction to ambient	TYP.	50	°C/W

## Ordering Information



## Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

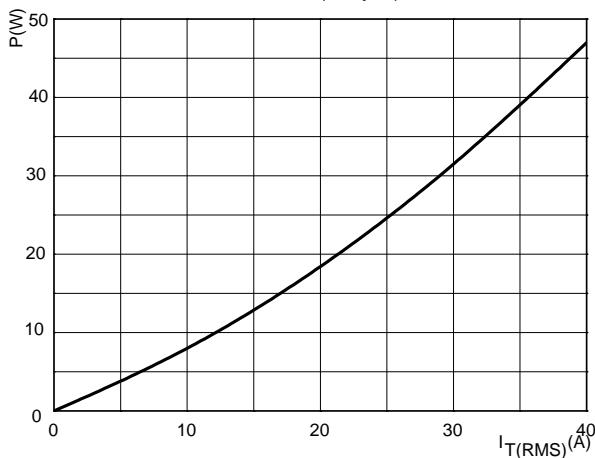


FIG.2: RMS on-state current versus case temperature (full cycle)

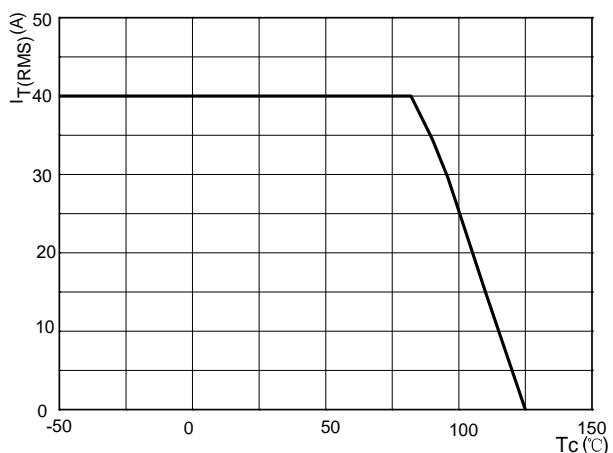


FIG.3: Surge peak on-state current versus number of cycles

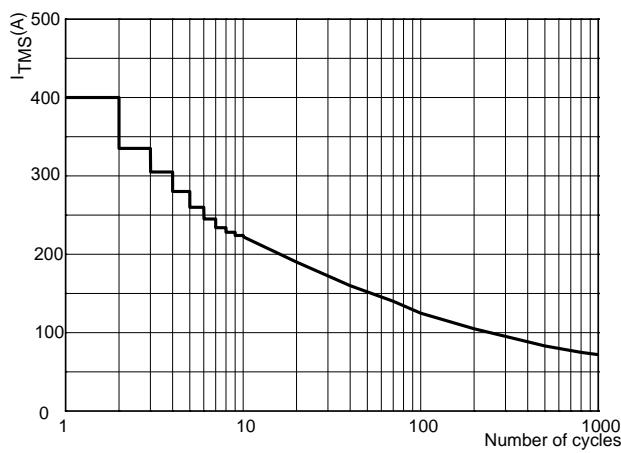


FIG.4: On-state characteristics (maximum values)

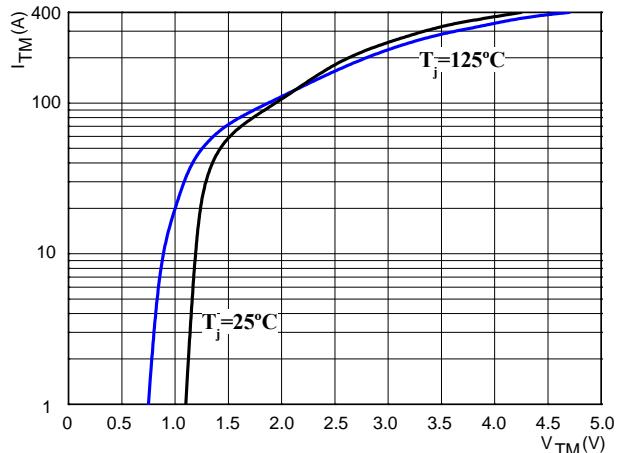


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ ms}$

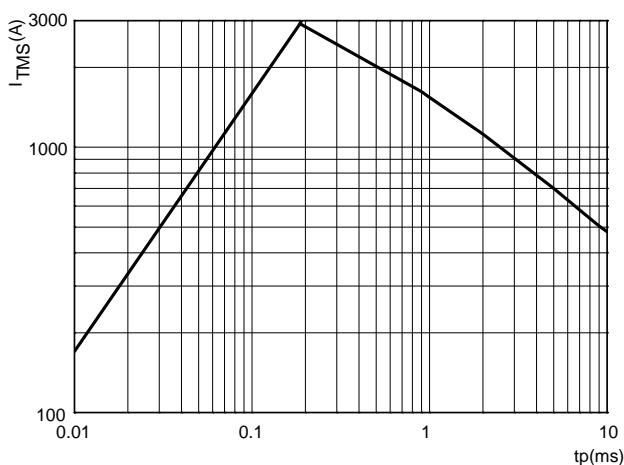
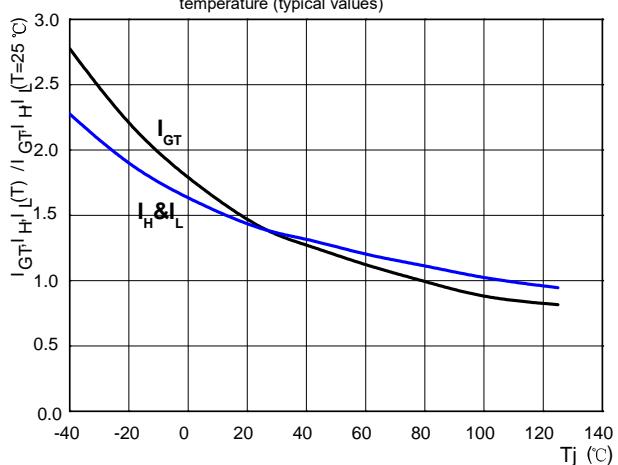


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



**Package Information**

**TO-3P**

